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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	2432
Number of Logic Elements/Cells	24320
Total RAM Bits	311296
Number of I/O	508
Number of Gates	1537000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k600efc672-2n

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

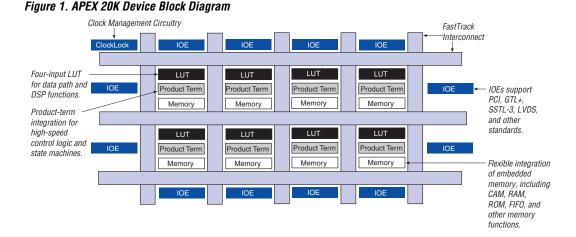
Feature	APEX 20K Devices	APEX 20KE Devices
MultiCore system integration	Full support	Full support
SignalTap logic analysis	Full support	Full support
32/64-Bit, 33-MHz PCI	Full compliance in -1, -2 speed grades	Full compliance in -1, -2 speed grades
32/64-Bit, 66-MHz PCI	-	Full compliance in -1 speed grade
MultiVolt I/O	2.5-V or 3.3-V V _{CCIO} V _{CCIO} selected for device Certain devices are 5.0-V tolerant	1.8-V, 2.5-V, or 3.3-V V _{CCIO} V _{CCIO} selected block-by-block 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction 2× and 4× clock multiplication	Clock delay reduction $m/(n \times v)$ or $m/(n \times k)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift LVDS support Up to four PLLs ClockShift, clock phase adjustment
Dedicated clock and input pins	Six	Eight
I/O standard support	2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI Low-voltage complementary metal-oxide semiconductor (LVCMOS) Low-voltage transistor-to-transistor logic (LVTTL)	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 2.5-V I/O 3.3-V PCI and PCI-X 3.3-V Advanced Graphics Port (AGP) Center tap terminated (CTT) GTL+ LVCMOS LVTTL True-LVDS and LVPECL data pins (in EP20K300E and larger devices) LVDS and LVPECL signaling (in all BGA and FineLine BGA devices) LVDS and LVPECL data pins up to 156 Mbps (in -1 speed grade devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	Dual-port RAM FIFO RAM ROM	CAM Dual-port RAM FIFO RAM ROM

Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack[®] Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20K device.

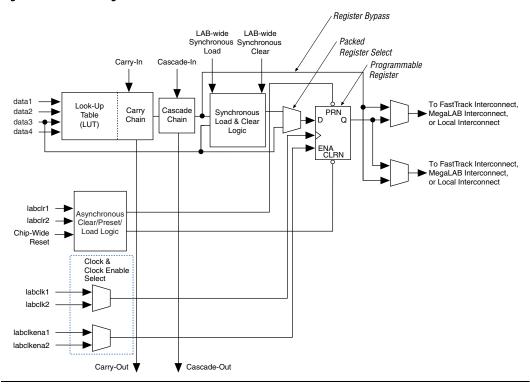


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Logic Element

The LE, the smallest unit of logic in the APEX 20K architecture, is compact and provides efficient logic usage. Each LE contains a four-input LUT, which is a function generator that can quickly implement any function of four variables. In addition, each LE contains a programmable register and carry and cascade chains. Each LE drives the local interconnect, MegaLAB interconnect, and FastTrack Interconnect routing structures. See Figure 5.

Figure 5. APEX 20K Logic Element



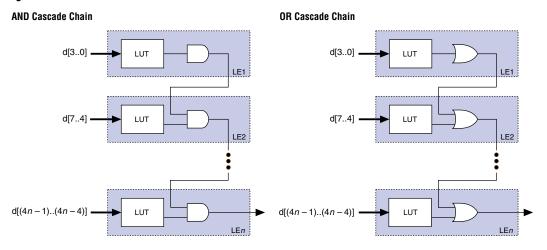
Each LE's programmable register can be configured for D, T, JK, or SR operation. The register's clock and clear control signals can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the register is bypassed and the output of the LUT drives the outputs of the LE.

Cascade Chain

With the cascade chain, the APEX 20K architecture can implement functions with a very wide fan-in. Adjacent LUTs can compute portions of a function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via De Morgan's inversion) to connect the outputs of adjacent LEs. Each additional LE provides four more inputs to the effective width of a function, with a short cascade delay. Cascade chain logic can be created automatically by the Quartus II software Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than ten LEs are implemented automatically by linking LABs together. For enhanced fitting, a long cascade chain skips alternate LABs in a MegaLAB structure. A cascade chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure. Figure 7 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in.

Figure 7. APEX 20K Cascade Chain



ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128×16 , 256×8 , 512×4 , $1,024 \times 2$, or $2,048 \times 1$. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128×16 RAM blocks can be combined to form a 128×32 RAM block, and two 512×4 RAM blocks can be combined to form a 512×8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 27 shows how a row IOE connects to the interconnect.

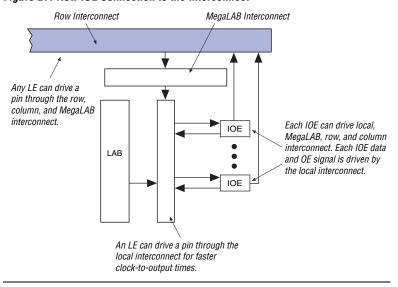


Figure 27. Row IOE Connection to the Interconnect

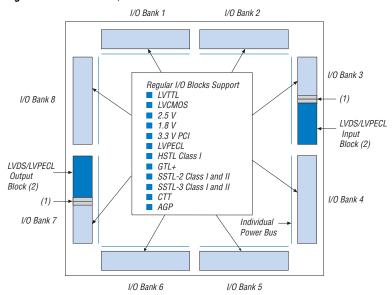


Figure 29. APEX 20KE I/O Banks

Notes to Figure 29:

- For more information on placing I/O pins in LVDS blocks, refer to the Guidelines for Using LVDS Blocks section in Application Note 120 (Using LVDS in APEX 20KE Devices).
- (2) If the LVDS input and output blocks are not used for LVDS, they can support all of the I/O standards and can be used as input, output, or bidirectional pins with V_{CCIO} set to 3.3 V, 2.5 V, or 1.8 V.

Power Sequencing & Hot Socketing

Because APEX 20K and APEX 20KE devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the $V_{\rm CCIO}$ and $V_{\rm CCINT}$ power supplies may be powered in any order.



For more information, please refer to the "Power Sequencing Considerations" section in the *Configuring APEX 20KE & APEX 20KC Devices* chapter of the *Configuration Devices Handbook*.

Signals can be driven into APEX 20K devices before and during power-up without damaging the device. In addition, APEX 20K devices do not drive out during power-up. Once operating conditions are reached and the device is configured, APEX 20K and APEX 20KE devices operate as specified by the user.

APEX 20KE devices also support the MultiVolt I/O interface feature. The APEX 20KE VCCINT pins must always be connected to a 1.8-V power supply. With a 1.8-V V_{CCINT} level, input pins are 1.8-V, 2.5-V, and 3.3-V tolerant. The VCCIO pins can be connected to either a 1.8-V, 2.5-V, or 3.3-V power supply, depending on the I/O standard requirements. When the VCCIO pins are connected to a 1.8-V power supply, the output levels are compatible with 1.8-V systems. When VCCIO pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and compatible with 3.3-V or 5.0-V systems. An APEX 20KE device is 5.0-V tolerant with the addition of a resistor.

Table 13 summarizes APEX 20KE MultiVolt I/O support.

Table 13. A	Table 13. APEX 20KE MultiVolt I/O Support Note (1)												
V _{CCIO} (V)		Input Sig	ınals (V)			Output S	ignals (V)						
	1.8	2.5	3.3	5.0	1.8	2.5	3.3	5.0					
1.8	✓	✓	✓		✓								
2.5	✓	✓	✓			✓							
3.3	✓	✓	\	(2)			√ (3)						

Notes to Table 13:

- The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}, except for the 5.0-V input case.
- (2) An APEX 20KE device can be made 5.0-V tolerant with the addition of an external resistor. You also need a PCI clamp and series resistor.
- (3) When $V_{CCIO} = 3.3 \text{ V}$, an APEX 20KE device can drive a 2.5-V device with 3.3-V tolerant inputs.

ClockLock & ClockBoost Features

APEX 20K devices support the ClockLock and ClockBoost clock management features, which are implemented with PLLs. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by sharing resources within the device. The ClockBoost circuitry allows the designer to distribute a low-speed clock and multiply that clock on-device. APEX 20K devices include a high-speed clock tree; unlike ASICs, the user does not have to design and optimize the clock tree. The ClockLock and ClockBoost features work in conjunction with the APEX 20K device's high-speed clock to provide significant improvements in system performance and band-width. Devices with an X-suffix on the ordering code include the ClockLock circuit.

The ClockLock and ClockBoost features in APEX 20K devices are enabled through the Quartus II software. External devices are not required to use these features.

Clock Phase & Delay Adjustment

The APEX 20KE ClockShift feature allows the clock phase and delay to be adjusted. The clock phase can be adjusted by 90° steps. The clock delay can be adjusted to increase or decrease the clock delay by an arbitrary amount, up to one clock period.

LVDS Support

Two PLLs are designed to support the LVDS interface. When using LVDS, the I/O clock runs at a slower rate than the data transfer rate. Thus, PLLs are used to multiply the I/O clock internally to capture the LVDS data. For example, an I/O clock may run at 105 MHz to support 840 megabits per second (Mbps) LVDS data transfer. In this example, the PLL multiplies the incoming clock by eight to support the high-speed data transfer. You can use PLLs in EP20K400E and larger devices for high-speed LVDS interfacing.

Lock Signals

The APEX 20KE ClockLock circuitry supports individual LOCK signals. The LOCK signal drives high when the ClockLock circuit has locked onto the input clock. The LOCK signals are optional for each ClockLock circuit; when not used, they are I/O pins.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the APEX 20K ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. In APEX 20KE devices, the clock input standard is programmable, so the PLL cannot respond to the clock until the device is configured. The PLL locks onto the input clock as soon as configuration is complete. Figure 30 shows the incoming and generated clock specifications.



For more information on ClockLock and ClockBoost circuitry, see *Application Note 115: Using the ClockLock and ClockBoost PLL Features in APEX Devices*.

The APEX 20K device instruction register length is 10 bits. The APEX 20K device USERCODE register length is 32 bits. Tables 20 and 21 show the boundary-scan register length and device IDCODE information for APEX 20K devices.

Table 20. APEX 20K Boundary-Sca	an Register Length
Device	Boundary-Scan Register Length
EP20K30E	420
EP20K60E	624
EP20K100	786
EP20K100E	774
EP20K160E	984
EP20K200	1,176
EP20K200E	1,164
EP20K300E	1,266
EP20K400	1,536
EP20K400E	1,506
EP20K600E	1,806
EP20K1000E	2,190
EP20K1500E	1 (1)

Note to Table 20:

(1) This device does not support JTAG boundary scan testing.

Table 22 shows the JTAG timing parameters and values for APEX 20K devices

Table 2	Table 22. APEX 20K JTAG Timing Parameters & Values									
Symbol	Parameter	Min	Max	Unit						
t _{JCP}	TCK clock period	100		ns						
t _{JCH}	TCK clock high time	50		ns						
t_{JCL}	TCK clock low time	50		ns						
t _{JPSU}	JTAG port setup time	20		ns						
t _{JPH}	JTAG port hold time	45		ns						
t _{JPCO}	JTAG port clock to output		25	ns						
t _{JPZX}	JTAG port high impedance to valid output		25	ns						
t _{JPXZ}	JTAG port valid output to high impedance		25	ns						
t _{JSSU}	Capture register setup time	20		ns						
t _{JSH}	Capture register hold time	45		ns						
t _{JSCO}	Update register clock to output		35	ns						
t _{JSZX}	Update register high impedance to valid output		35	ns						
t _{JSXZ}	Update register valid output to high impedance		35	ns						



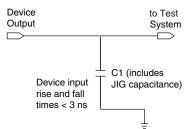
For more information, see the following documents:

- Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)
- Jam Programming & Test Language Specification

Generic Testing

Each APEX 20K device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for APEX 20K devices are made under conditions equivalent to those shown in Figure 32. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 32. APEX 20K AC Test Conditions Note (1)



Note to Figure 32:

(1) Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result.

Operating Conditions

Tables 23 through 26 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V APEX 20K devices.

Table 2	Table 23. APEX 20K 5.0-V Tolerant Device Absolute Maximum Ratings Notes (1), (2)										
Symbol	Parameter	Conditions	Min	Max	Unit						
V _{CCINT}	Supply voltage	With respect to ground (3)	-0.5	3.6	V						
V _{CCIO}			-0.5	4.6	V						
V _I	DC input voltage		-2.0	5.75	V						
I _{OUT}	DC output current, per pin		-25	25	mA						
T _{STG}	Storage temperature	No bias	-65	150	° C						
T _{AMB}	Ambient temperature	Under bias	-65	135	° C						
TJ	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C						
		Ceramic PGA packages, under bias		150	° C						

Table 2	8. APEX 20KE Device Recommende	d Operating Conditions			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	1.71 (1.71)	1.89 (1.89)	V
V _{CCIO}	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	(3), (4)	1.71 (1.71)	1.89 (1.89)	V
VI	Input voltage	(5), (6)	-0.5	4.0	٧
V _O	Output voltage		0	V _{CCIO}	V
TJ	Junction temperature	For commercial use	0	85	°C
		For industrial use	-40	100	°C
t _R	Input rise time			40	ns
t _F	Input fall time			40	ns

Tables 40 through 42 show the $f_{\mbox{\scriptsize MAX}}$ timing parameters for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Symbol	-1 Speed Grade		-2 Spee	-2 Speed Grade		-3 Speed Grade	
	Min	Max	Min	Max	Min	Max	
t _{SU}	0.5		0.6		0.8		ns
t _H	0.7		0.8		1.0		ns
t _{CO}		0.3		0.4		0.5	ns
t _{LUT}		0.8		1.0		1.3	ns
t _{ESBRC}		1.7		2.1		2.4	ns
t _{ESBWC}		5.7		6.9		8.1	ns
t _{ESBWESU}	3.3		3.9		4.6		ns
t _{ESBDATASU}	2.2		2.7		3.1		ns
t _{ESBDATAH}	0.6		0.8		0.9		ns
t _{ESBADDRSU}	2.4		2.9		3.3		ns
t _{ESBDATACO1}		1.3		1.6		1.8	ns
t _{ESBDATACO2}		2.6		3.1		3.6	ns
t _{ESBDD}		2.5		3.3		3.6	ns
t _{PD}		2.5		3.0		3.6	ns
t _{PTERMSU}	2.3		2.6		3.2		ns
t _{PTERMCO}		1.5		1.8		2.1	ns
t _{F1-4}		0.5		0.6		0.7	ns
t _{F5-20}		1.6		1.7		1.8	ns
t _{F20+}		2.2		2.2		2.3	ns
t _{CH}	2.0		2.5		3.0		ns
t _{CL}	2.0		2.5		3.0		ns
t _{CLRP}	0.3		0.4		0.4		ns
t _{PREP}	0.5		0.5		0.5		ns
t _{ESBCH}	2.0		2.5		3.0		ns
t _{ESBCL}	2.0		2.5		3.0		ns
t _{ESBWP}	1.6		1.9		2.2		ns
t _{ESBRP}	1.0		1.3		1.4		ns

Symbol	-1	-1		-2		-3	
	Min	Max	Min	Max	Min	Max	
t _{CH}	0.55		0.78		1.15		ns
t _{CL}	0.55		0.78		1.15		ns
t _{CLRP}	0.22		0.31		0.46		ns
t _{PREP}	0.22		0.31		0.46		ns
t _{ESBCH}	0.55		0.78		1.15		ns
t _{ESBCL}	0.55		0.78		1.15		ns
t _{ESBWP}	1.43		2.01		2.97		ns
t _{ESBRP}	1.15		1.62		2.39		ns

Symbol		-1		-2		3	Unit
	Min	Max	Min	Max	Min	Max	
t _{INSU}	2.02		2.13		2.24		ns
t _{INH}	0.00		0.00		0.00		ns
t _{outco}	2.00	4.88	2.00	5.36	2.00	5.88	ns
t _{INSUPLL}	2.11		2.23		=		ns
t _{INHPLL}	0.00		0.00		=		ns
t _{OUTCOPLL}	0.50	2.60	0.50	2.88	-	-	ns

Symbol	-	1	-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR}	1.85		1.77		1.54		ns
t _{INHBIDIR}	0.00		0.00		0.00		ns
t _{OUTCOBIDIR}	2.00	4.88	2.00	5.36	2.00	5.88	ns
t _{XZBIDIR}		7.48		8.46		9.83	ns
t _{ZXBIDIR}		7.48		8.46		9.83	ns
t _{INSUBIDIRPLL}	4.12		4.24		=		ns
t _{INHBIDIRPLL}	0.00		0.00		-		ns
t _{OUTCOBIDIRPLL}	0.50	2.60	0.50	2.88	-	-	ns
t _{XZBIDIRPLL}		5.21		5.99		-	ns
t _{ZXBIDIRPLL}		5.21		5.99		-	ns

Tables 67 through 72 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K160E APEX 20KE devices.

Table 67. EP2	Table 67. EP20K160E f _{MAX} LE Timing Microparameters											
Symbol	_	1		-2	-	3	Unit					
	Min	Max	Min	Max	Min	Max						
t _{SU}	0.22		0.24		0.26		ns					
t _H	0.22		0.24		0.26		ns					
t _{CO}		0.25		0.31		0.35	ns					
t _{LUT}		0.69		0.88		1.12	ns					

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	1
t _{INSUBIDIR}	2.86		3.24		3.54		ns
t _{INHBIDIR}	0.00		0.00		0.00		ns
t _{OUTCOBIDIR}	2.00	5.07	2.00	5.59	2.00	6.13	ns
t _{XZBIDIR}		7.43		8.23		8.58	ns
t _{ZXBIDIR}		7.43		8.23		8.58	ns
t _{INSUBIDIRPLL}	4.93		5.48		-		ns
t _{INHBIDIRPLL}	0.00		0.00		-		ns
toutcobidirpll	0.50	3.00	0.50	3.35	-	-	ns
t _{XZBIDIRPLL}		5.36		5.99		-	ns
t _{ZXBIDIRPLL}		5.36		5.99		-	ns

Tables 73 through 78 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K200E APEX 20KE devices.

Table 73. EP20K200E f _{MAX} LE Timing Microparameters									
Symbol	-1		-2		-3		Unit		
	Min	Max	Min	Max	Min	Max			
t _{SU}	0.23		0.24		0.26		ns		
t _H	0.23		0.24		0.26		ns		
t_{CO}		0.26		0.31		0.36	ns		
t _{LUT}		0.70		0.90		1.14	ns		

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	1
t _{ESBARC}		1.78		2.02		1.95	ns
t _{ESBSRC}		2.52		2.91		3.14	ns
t _{ESBAWC}		3.52		4.11		4.40	ns
t _{ESBSWC}		3.23		3.84		4.16	ns
t _{ESBWASU}	0.62		0.67		0.61		ns
t _{ESBWAH}	0.41		0.55		0.55		ns
t _{ESBWDSU}	0.77		0.79		0.81		ns
t _{ESBWDH}	0.41		0.55		0.55		ns
t _{ESBRASU}	1.74		1.92		1.85		ns
t _{ESBRAH}	0.00		0.01		0.23		ns
t _{ESBWESU}	2.07		2.28		2.41		ns
t _{ESBWEH}	0.00		0.00		0.00		ns
t _{ESBDATASU}	0.25		0.27		0.29		ns
t _{ESBDATAH}	0.13		0.13		0.13		ns
t _{ESBWADDRSU}	0.11		0.04		0.11		ns
t _{ESBRADDRSU}	0.14		0.11		0.16		ns
t _{ESBDATACO1}		1.29		1.50		1.63	ns
t _{ESBDATACO2}		2.55		2.99		3.22	ns
t _{ESBDD}		3.12		3.57		3.85	ns
t _{PD}		1.84		2.13		2.32	ns
t _{PTERMSU}	1.08		1.19		1.32		ns

1.53

1.66

ns

1.31

 t_{PTERMCO}

Version 4.1

APEX 20K Programmable Logic Device Family Data Sheet version 4.1 contains the following changes:

- t_{ESBWEH} added to Figure 37 and Tables 35, 50, 56, 62, 68, 74, 86, 92, 97, and 104.
- Updated EP20K300E device internal and external timing numbers in Tables 79 through 84.



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